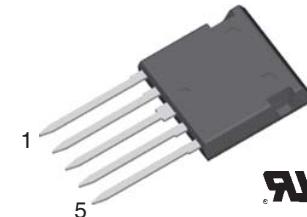
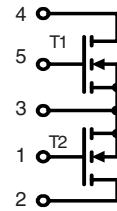


HiPerFET™ Power MOSFET

Common Source Topology
in ISOPLUS i4-PAC™

I_{D25} = 75 A
 V_{DSS} = 100 V
 $R_{DSon\ typ.}$ = 18 mΩ

Preliminary data

**MOSFET T1/T2**

Symbol	Conditions	Maximum Ratings		
V_{DSS}	$T_{VJ} = 25^\circ C$ to $150^\circ C$	100	V	
V_{GS}		± 20	V	
I_{D25}	$T_C = 25^\circ C$	75	A	
I_{D90}	$T_C = 90^\circ C$	50	A	
I_{F25}	(body diode) $T_C = 25^\circ C$	100	A	
I_{F90}	(body diode) $T_C = 90^\circ C$	60	A	
dv/dt	$V_{DS} < V_{DSS}$; $I_F \leq 300A$; $ di_F/dt \leq 100A/\mu s$; $R_G = 2\Omega$ $T_{VJ} = 150^\circ C$	5	V/ns	
E_{AR}	$T_C = 25^\circ C$	30	mJ	

Symbol	Conditions	Characteristic Values		
		($T_{VJ} = 25^\circ C$, unless otherwise specified)	min.	typ.
R_{DSon}	$V_{GS} = 10 V$; $I_D = I_{D90}$		18	25 mΩ
V_{GSth}	$V_{DS} = 20 V$; $I_D = 4 mA$	2		4 V
I_{DSS}	$V_{DS} = V_{DSS}$; $V_{GS} = 0 V$; $T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		0.25	0.3 mA mA
I_{GSS}	$V_{GS} = \pm 20 V$; $V_{DS} = 0 V$		200	nA
Q_g Q_{gs} Q_{gd}	$V_{GS} = 10 V$; $V_{DS} = 0.5 \cdot V_{DSS}$; $I_D = I_{D90}$		180 35 85	nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 V$; $V_{DS} = 0.5 \cdot V_{DSS}$ $I_D = I_{D90}$; $R_G = 2 \Omega$		20 60 80 60	ns ns ns ns
V_F	(body diode) $I_F = 75 A$; $V_{GS} = 0 V$	1.2	1.5	V
t_{rr}	(body diode) $I_F = 37.5 A$; $-di/dt = 100A/\mu s$; $V_{DS} = 25V$	300		ns
R_{thJC} R_{thJH}	with heat transfer paste		0.93	0.5 K/W K/W

IXYS reserves the right to change limits, test conditions and dimensions.

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Component

Symbol	Conditions	Maximum Ratings		
		min.	typ.	max.
T_{VJ}		-55...+150		°C
T_{stg}		-55...+125		°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500		V~
F_c	mounting force with clip	20...120		N
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C_p	coupling capacity between shorted pins and mounting tab in the case	40		pF
d_s, d_A	pin - pin	1.7		mm
d_s, d_A	pin - backside metal	5.5		mm
Weight				

Dimensions in mm (1 mm = 0.0394")